

2SD1850

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Silicon NPN Triple-Diffused Planar Type

Horizontal Deflection Output

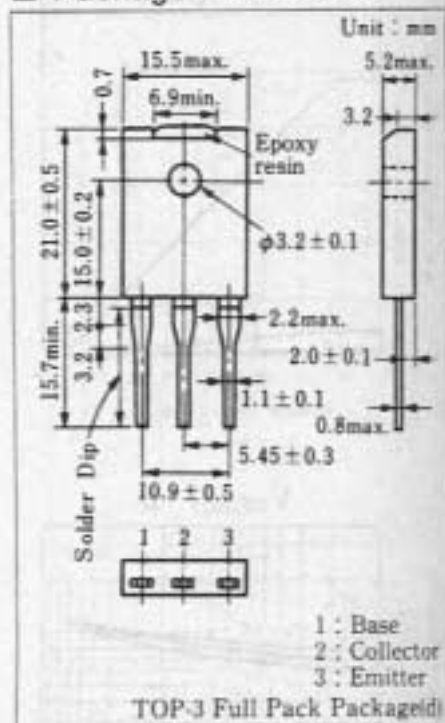
■ Features

- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
	V _{CES}	1500	V
Collector-emitter voltage	V _{CE0}	700	V
	V _{EBO}	7	V
Peak collector current	I _{CP}	20	A
Collector current	I _C	7	A
Base current	I _B	3	A
Collector power dissipation	T _c = 25°C	120	W
	T _a = 25°C	3	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

■ Package Dimensions



■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CB0}	V _{CB} = 1000V, I _E = 0			10	μA
		V _{CB} = 1500V, I _E = 0			1	mA
Emitter-base voltage	V _{EBO}	I _E = 1mA, I _C = 0		7		V
DC current gain	h _{FE1}	V _{CE} = 5V, I _C = 1A	5		25	
	h _{FE2}	V _{CE} = 5V, I _C = 6A	4.5			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 6A, I _B = 1.5A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 6A, I _B = 1.5A			1.5	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 1A, f = 0.5MHz		2		MHz
Storage time (L load)	t _{stg}	I _C = 6A, I _{B1} = 1.5A			11	μs
Collector current fall time (L load)	t _f	I _{B2} = -1.5A, L _{break} = 5μH			0.8	μs
Storage time (R load)	t _{stg}	I _C = 6A, I _{B1} = 1.5A		1.5		μs
Collector current fall time (R load)	t _f	I _{B2} = -3A, V _{CC} = 200V		0.2		μs

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